

MOS Fied Effect Transistor

2SJ204

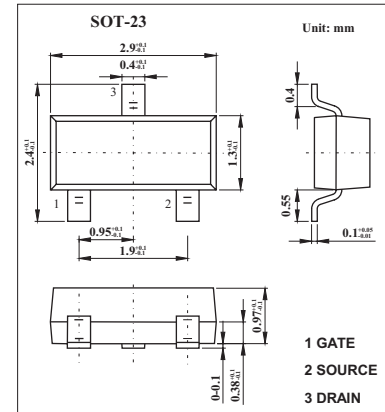
■ Features

- Directly driven by lcs having a 5V poer supply.

- Has low on-state resistance

$R_{DS(on)}=13\ \Omega$ MAX.@ $V_{GS}=-4.0V, I_D=-10mA$

$R_{DS(on)}=8\ \Omega$ MAX.@ $V_{GS}=-10V, I_D=-10mA$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage $V_{GS}=0$	V_{DSS}	-30	V
Gate to source voltage $V_{DS}=0$	V_{GSS}	± 20	V
Drain current (DC)	I_D	± 200	mA
Drain current(pulse) *	I_D	± 400	mA
Power dissipation	P_D	200	m W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10\text{ ms}$; $d \leq 50\%$.

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0$			-10	$\mu\text{ A}$
Gate leakage current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0$			± 1.0	$\mu\text{ A}$
Gate cut-off voltage	$V_{GS(off)}$	$V_{DS}=-5.0V, I_D=-1\ \mu\text{ A}$	-1.4	-1.9	-2.4	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=-5.0V, I_D=-10mA$	20			ms
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=-4V, I_D=-10mA$		8.5	13	Ω
		$V_{GS}=-10V, I_D=-10mA$		5	8	Ω
Input capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0, f=1MHz$		27		pF
Output capacitance	C_{oss}			27		pF
Reverse transfer capacitance	C_{rss}			6		pF
Turn-on delay time	$t_{d(on)}$				120	
Rise time	t_r	$V_{GS(on)}=-4V, R_G=10\ \Omega, V_{DD}=-5V, I_D=-0.3A, R_L=1.5\ \Omega$		240		ns
Turn-off delay time	$t_{d(off)}$			135		ns
Fall time	t_f				210	

■ Marking

Marking	H15
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